

## **isc Silicon NPN Power Transistor**

# 2SC4881

#### DESCRIPTION

- Collector-Emitter Breakdown Voltage-: V<sub>(BR)CEO</sub>= 50V(Min)
- High Switching Speed
- Low Collector Saturation Voltage-
  - :  $V_{CE(sat)}$  0.4V(Max)@ (I<sub>C</sub>= 2.5A, I<sub>B</sub>= 125mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

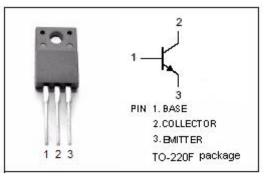
#### **APPLICATIONS**

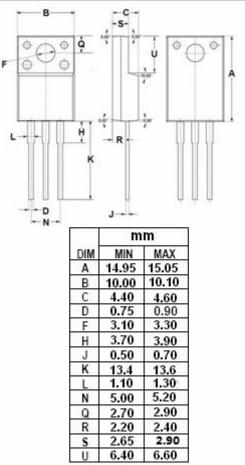
· Designed for high current switching applications.

SYMBOL	PARAMETER	VALUE	UNIT	
Vсво	Collector-Base Voltage	60	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
Ic	Collector Current-Continuous	5	A	
I <sub>CM</sub>	Collector Current-Pulse	8	A	
I <sub>B</sub>	Base Current-Continuous	1	А	
5	Total Power Dissipation @Tc=25℃	20		
Ρ <sub>T</sub>	Total Power Dissipation @T <sub>a</sub> =25°C	2.0	W	
TJ	Junction Temperature	<b>150</b> ℃		
T <sub>stg</sub>	Storage Temperature	- <b>55~150</b> ℃		

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### ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)





isc Website: www.iscsemi.cn

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## INCHANGE SEMICONDUCTOR

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## ELECTRICAL CHARACTERISTICS

#### Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	50			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2.5A; I <sub>B</sub> = 125mA			0.4	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2.5A; I <sub>B</sub> = 125mA			1.3	V
І <sub>сво</sub>	Collector Cutoff Current	V <sub>CB</sub> = 50V ; I <sub>E</sub> = 0			1	μA
І <sub>ЕВО</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0			1	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 1V	100		320	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 2.5A ; V <sub>CE</sub> = 1V	60			
Сов	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V; f= 1.0MHz		45		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 4V		100		MHz

Switching times

ton	Turn-on Time		0.1	μ S
t <sub>stg</sub>	Storage Time	$ \begin{array}{c} R_{L}\text{=}~12~\Omega, I_{B1}\text{=}~\text{-}I_{B2}\text{=}~125 \text{mA}, \\ V_{CC}\text{=}~30 V \end{array} $	0.8	μ <b>S</b>
t <sub>f</sub>	Fall Time		0.1	μ5

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